Amendments to the Specification:

Please replace the paragraph beginning on page 3, line 16, with the following amended paragraph:

The layer thickness of the dielectric layer $\underline{d_{medium}}$ having the dielectric constant ϵ_{medium} should preferably be selected such that

$$\frac{\varepsilon_{\text{medium}} \cdot d_{\varepsilon}}{\varepsilon \cdot d_{\text{medium}}} > 5$$

so that the metallization structure that is next in the vertical direction is well decoupled. In respect of the decoupling in the horizontal direction, the following should apply

$$\frac{\varepsilon_{\text{medium}} \cdot d_{\text{min}}}{d_{\text{medium}} \cdot \varepsilon} > 7$$

where d_{min} is the minimum distance to the next metallization structure in the plane.